

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

ULN2003

Product specification

General Description

The ULN2003 is high-voltage high-current Darlington transistor arrays each containing seven open collector common emitter pairs. Each pair is rated at 500mA. Suppression diodes are included for inductive load driving, the inputs and outputs are pinned in opposition to simplify board layout.






These devices are capable of driving a wide range of loads including solenoids, relays, DC motors, LED displays, filament lamps, thermal print-heads and high-power buffers.

The ULN2003 is available in both a small outline 16-pin package (DIP-16, SOP16 , TSSOP16).

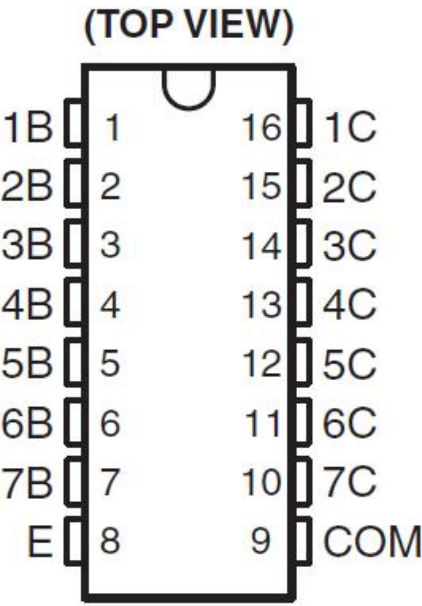
Features

- 500-mA-Rated Collector Current(single output)
- High-Voltage Outputs:50V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay-Driver Applications

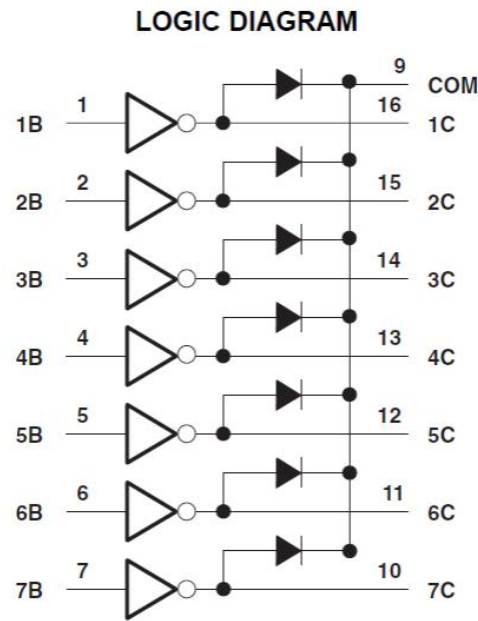
Encapsulation form and pin definition function

PACKAGE OUTLINE	Marking
 SOP-16	
 TSSOP16	
 DIP-16	

Pin Assignments



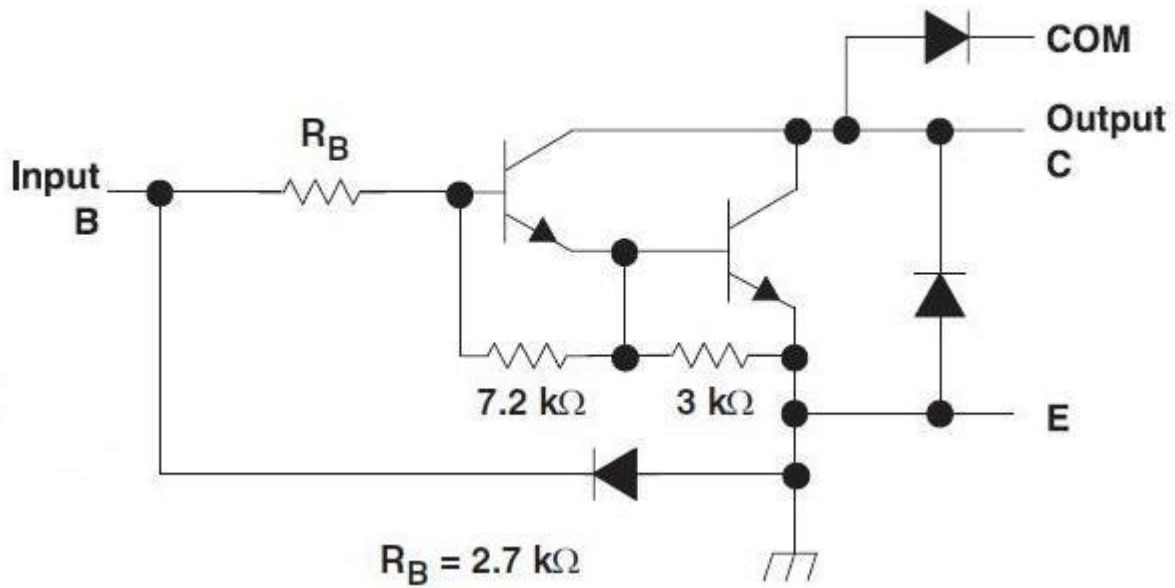
Connection Diagram



Pin Descriptions

Pin Number	Pin Name	Function
1	1B	Input pair1
2	2B	Input pair1
3	3B	Input pair1
4	4B	Input pair1
5	5B	Input pair1
6	6B	Input pair1
7	7B	Input pair1
8	E	Common Emitter (ground)
9	COM	Common Clamp Diodes
10	7C	Output pair7
11	6C	Output pair6
12	5C	Output pair5
13	4C	Output pair4
14	3C	Output pair3
15	2C	Output pair2
16	1C	Output pair1

Functional Block Diagram



Note: All resistor values shown are nominal.

The collector-emitter diode is a parasitic structure and should not be used to conduct current. If the collector(s) go below ground an external Schottky diode should be added to clamp negative undershoots.

Order Information

Designator	Package	Packing type
ULN2003ALDTR-MS	SOP-16	3500
ULN2003ALPWR-MS	TSSOP16	4000
ULN2003AN-MS	DIP-16	25

Absolute Maximum Ratings ⁽¹⁾

At 25°C free-air temperature (unless otherwise noted)

Symbol	Parameter		Min	Max	Unit
V _{CC}	Collector to emitter voltage			50	V
V _R	Clamp diode reverse voltage(2)			50	V
V _I	Input voltage(2)			30	V
I _{CP}	Peak collector current	See typical characteristics		500	mA
I _{OK}	Output clamp current			500	mA
I _{TE}	Total emitter-terminal current			-2.5	A
T _A	Operating free-air temperature range	ULN2003Axxx-MS	-40	+105	°C
θ _{JA}	Thermal Resistance Junction-to-Ambient(3)			63	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case(4)			12	
T _J	Operating virtual junction temperature			+150	°C
T _{STG}	Storage temperature range		-65	+150	°C
ESD	Human Body Mode		--	3000	V

(1) =Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device.

These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

(3) Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $PD = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

(4) Maximum power dissipation is a function of T_J(max), θ_{JC}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $PD = (T_J(max) - T_A)/\theta_{JC}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{CC}	Collector to Emitter voltage	-	50	V
T _A	Operating Ambient Temperature	-40	+105	°C

Electrical Characteristics(TA=+25°C, unless otherwise specified)

Parameter		Test Figure	Test Conditions		ULN2003			Unit
					MIN	TYP	MAX	
$V_{I(on)}$	On-state input voltage	Figure 6	$V_{CE} = 2\text{ V}$	$I_C = 200\text{ mA}$	--	--	2.4	V
				$I_C = 250\text{ mA}$	--	--	2.7	
				$I_C = 300\text{ mA}$	--	--	3	
$V_{CE(sat)}$	Collector-emitter saturation voltage	Figure 5	$I_I = 250\text{ }\mu\text{A}$,	$I_C = 100\text{ mA}$	--	0.9	1.1	V
			$I_I = 350\text{ }\mu\text{A}$,	$I_C = 200\text{ mA}$	--	1	1.3	
			$I_I = 500\text{ }\mu\text{A}$,	$I_C = 350\text{ mA}$	--	1.2	1.6	
I_{CEX}	Collector cutoff current	Figure 1	$V_{CE} = 50\text{ V}$,	$I_I = 0$	--	--	50	μA
		Figure 2	$V_{CE} = 50\text{ V}$, $T_A = +105^\circ\text{C}$	$I_I = 0$	--	--	100	
V_F	Clamp forward voltage	Figure 8	$I_F = 350\text{ mA}$		--	1.7	2	V
$I_{I(off)}$	Off-state input current	Figure 3	$V_{CE} = 50\text{ V}$,	$I_C = 500\text{ }\mu\text{A}$	50	65	--	μA
I_I	Input current	Figure 4	$V_I = 3.85\text{ V}$		--	0.93	1.35	mA
			$V_I = 5\text{ V}$		--	--	--	
			$V_I = 12\text{ V}$		--	--	--	
I_R	Clamp reverse current	Figure 7	$V_R = 50\text{ V}$		--	--	50	μA
				$T_A = 70^\circ\text{C}$	--	--	100	
C_i	Input capacitance		$V_I = 0$, $f = 1\text{ MHz}$		--	15	25	pF

Switching Characteristics (TA = +25°C, unless otherwise specified)

Parameter		Test Conditions	ULN2003			UNIT
			MIN	TYP	MAX	
t_{PLH}	Propagation delay time, low- to high-level output	See Figure 9		0.25	1	μs
t_{PHL}	Propagation delay time, high- to low-level output	See Figure 9		0.25	1	μs
V_{OH}	High-level output voltage after switching	$V_S = 50\text{ V}$, $I_O = 300\text{ mA}$, See Figure 9	$V_S - 20$			mV

Parameter Measurement Information

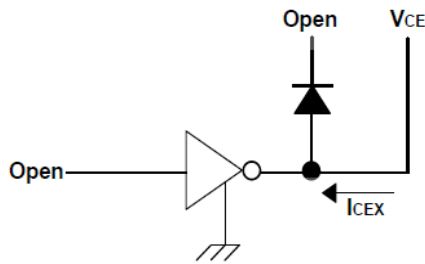


Fig.1 I_{CEX} Test Circuit

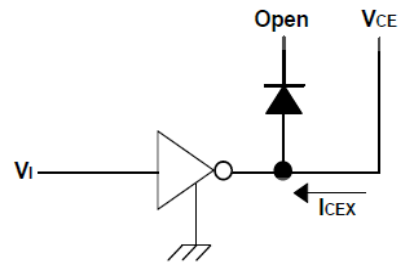


Fig.2 I_{CEX} Test Circuit

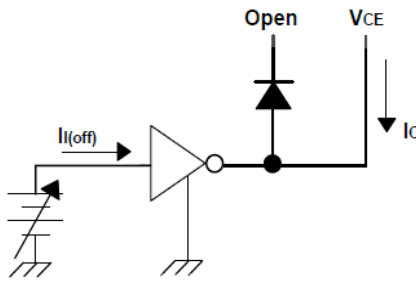


Fig.3 $I_{I(off)}$ Test Circuit

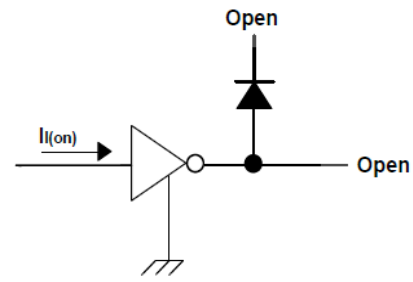


Fig.4 I_I Test Circuit

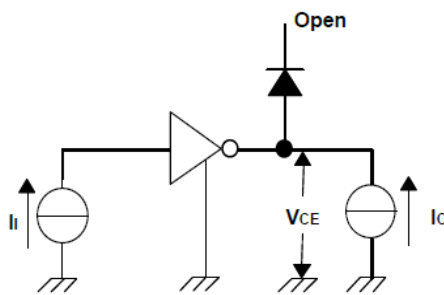


Fig.5 h_{FE} , $V_{CE(sat)}$ Test Circuit

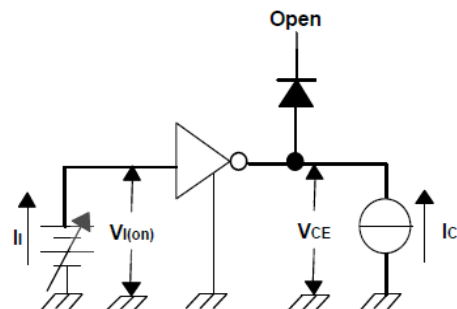


Fig.6 $V_{I(on)}$ Test Circuit

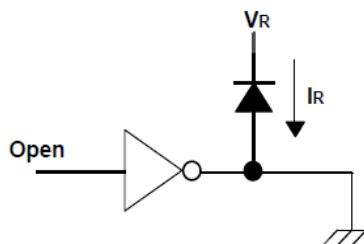


Fig.7 I_R Test Circuit

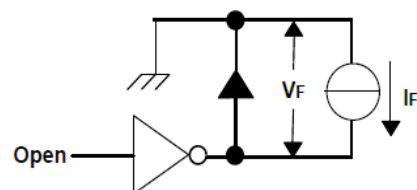


Fig.8 V_F Test Circuit

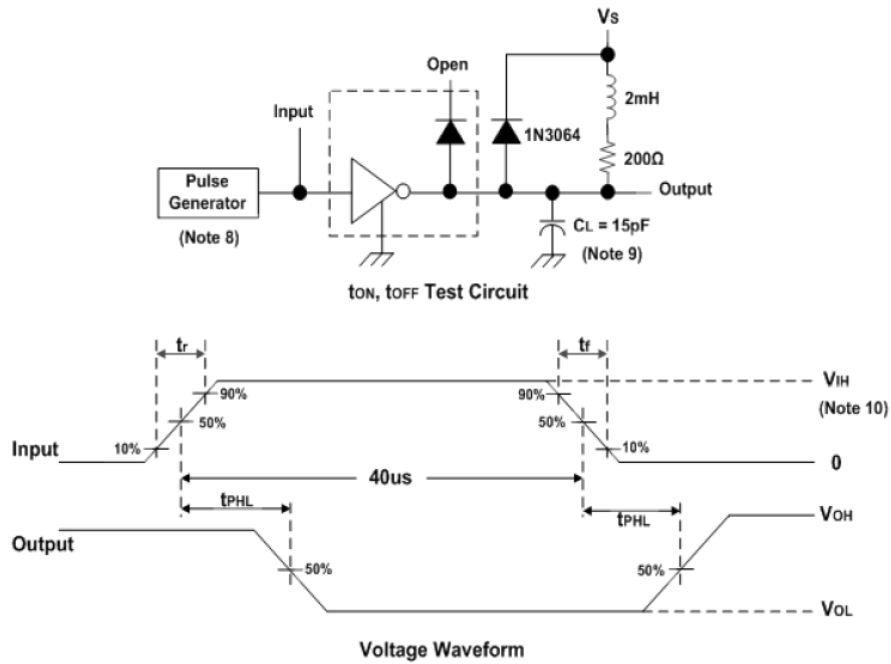


Fig. 9 Latch-Up Test Circuit and Voltage Waveform

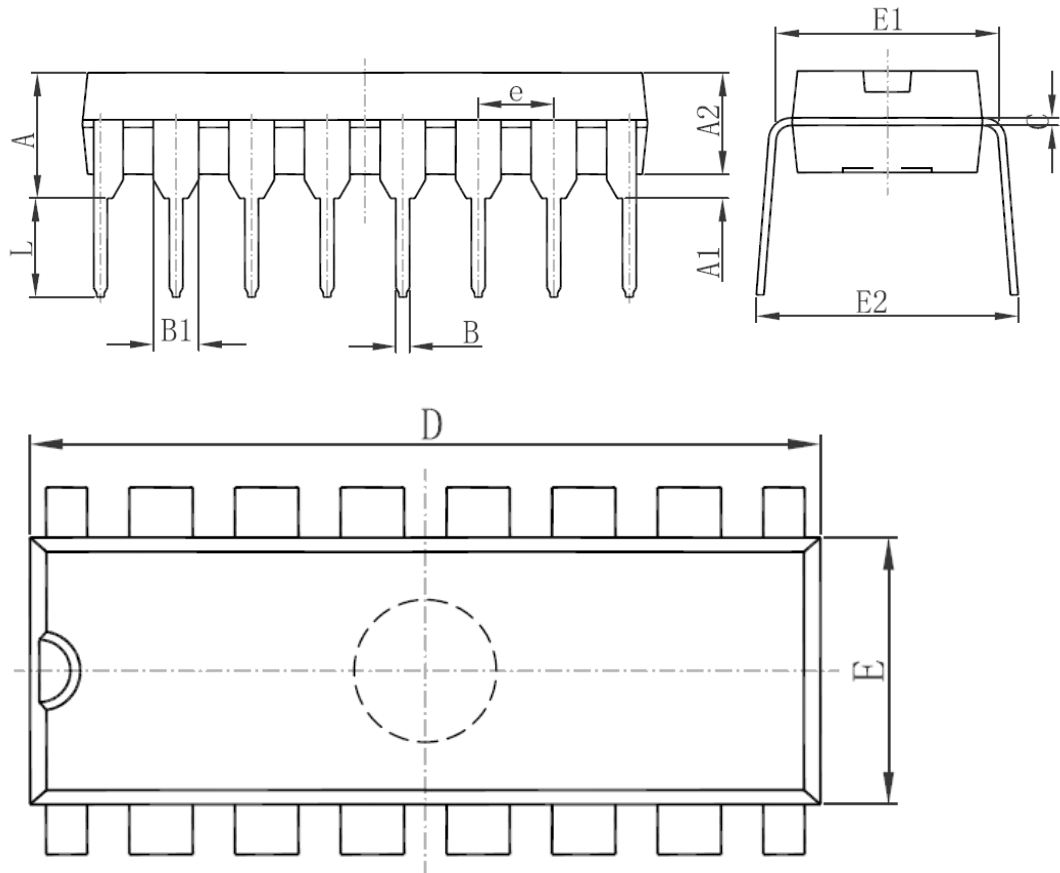
Notes: 8. The pulse generator has the following characteristics:

Pulse Width=12.5Hz, output impedance 50Ω, $t_r \leq 5\text{ns}$, $t_f \leq 10\text{ns}$.

9. C_L includes probe and jig capacitance.

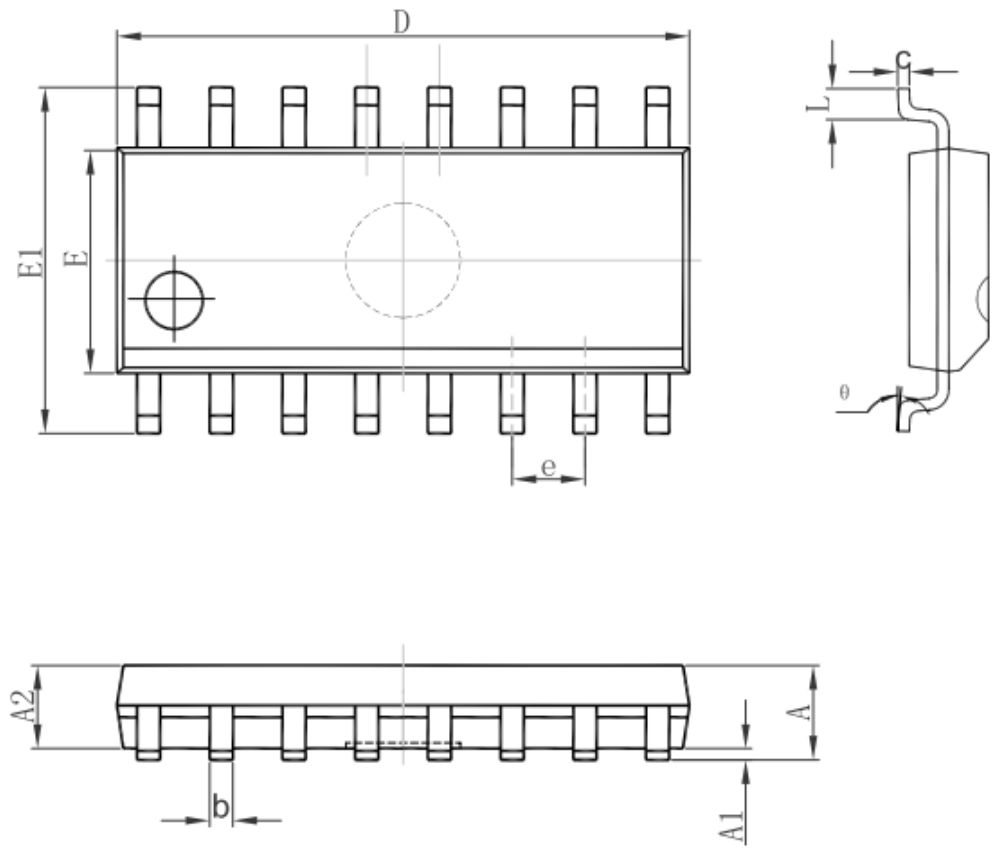
10. $V_{IH}=3\text{V}$

DIP-16Outline Dimensions



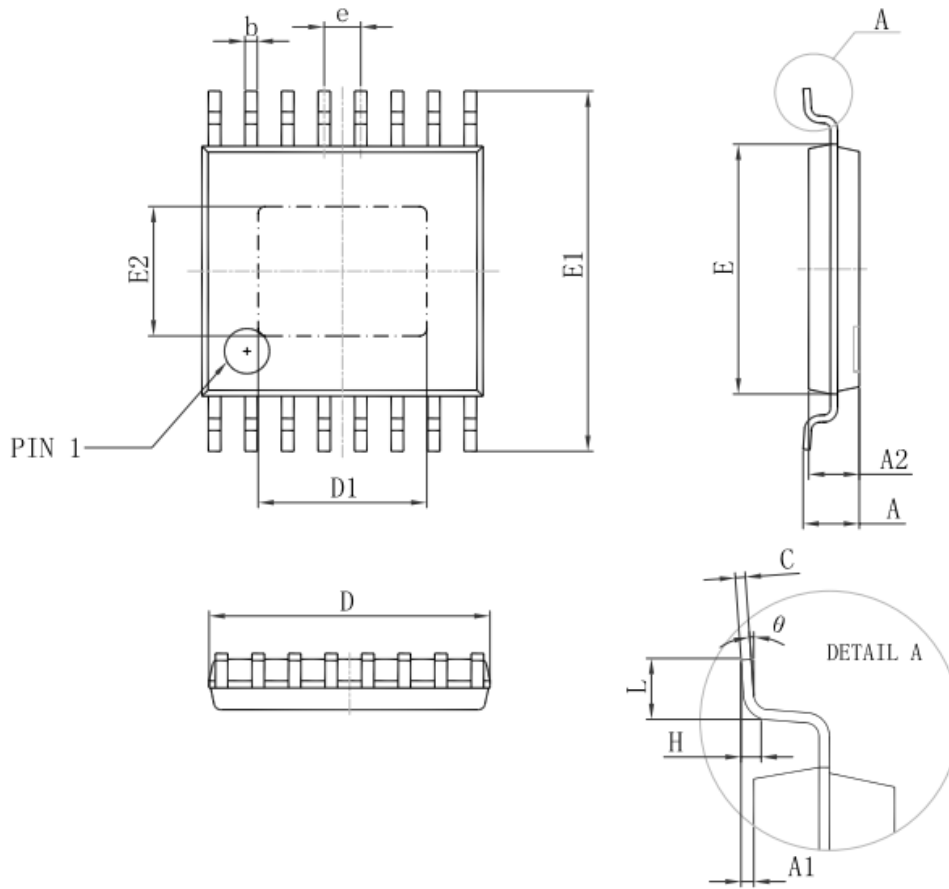
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.710	4.310	0.146	0.170
A1	0.510		0.020	
A2	3.200	3.600	0.126	0.142
B	0.380	0.570	0.015	0.022
B1	1.524 (BSC)		0.060 (BSC)	
C	0.204	0.360	0.008	0.014
D	18.800	19.200	0.740	0.756
E	6.200	6.600	0.244	0.260
E1	7.320	7.920	0.288	0.312
e	2.540 (BSC)		0.100 (BSC)	
L	3.000	3.600	0.118	0.142
E2	8.400	9.000	0.331	0.354

SOP-16 Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	9.800	10.200	0.386	0.402
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

TSSOP16 Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	4.900	5.100	0.193	0.201
D1	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
e	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
E2	2.200	2.400	0.087	0.094
A		1.150		0.043
A2	0.800	1.000	0.031	0.039
A1	0.020	0.150	0.001	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.02	0.028
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specification of any and all MSKSEMI Semiconductor products described or contained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.